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**Amendments to th Claims**

1. (previously presented) A semiconductor device comprising:  
a source and a drain, said source and drain consisting essentially of silicide;  
a semiconductor body disposed between the source and the drain;  
a gate electrode disposed over the body and defining a channel interposed  
between the source and the drain; and  
a gate dielectric separating the gate electrode and the body, said gate dielectric  
being made from a material having a relative permittivity of greater than about 10.
2. (original) The semiconductor device according to claim 1, wherein the  
semiconductor device is configured as a MOSFET.
3. (original) The semiconductor device according to claim 1, wherein the gate is  
comprised of a metal containing material.
4. (original) The semiconductor device according to claim 3, wherein the gate  
electrode is composed of one or more materials selected from titanium nitride, tantalum  
nitride, tungsten, tantalum, aluminum, nickel, ruthenium, rhodium, palladium, platinum  
and combinations thereof.
5. (currently amended) The semiconductor device according to claim 1, wherein  
the ~~high-K material~~ gate dielectric is composed of one or more materials selected from  
hafnium oxide, zirconium oxide, cerium oxide, aluminum oxide, titanium oxide, yttrium  
oxide, barium strontium titanate and mixtures thereof.
6. (original) The semiconductor device according to claim 1, further comprising  
a buffer interface disposed between the body and the gate dielectric.
7. (original) The semiconductor device according to claim 6, wherein the buffer  
interface is formed from an oxide having a thickness of about 0.5 nm to about 0.7 nm.

8. (original) The semiconductor device according to claim 1, wherein the silicide of the source and the drain is formed by reacting nickel with a layer of semiconductor material, the body being formed from the layer of semiconductor material.

9. (original) The semiconductor device according to claim 1, further comprising a liner disposed adjacent sidewalls defined by the gate electrode and gate dielectric.

10. (original) The semiconductor device according to claim 1, wherein the body is formed from a semiconductor film disposed on an insulating layer, the insulating layer being disposed on a semiconductor substrate.

11-19. (cancelled)

20. (previously presented) A semiconductor device comprising:  
a source and a drain, said source and drain consisting essentially of silicide;  
a semiconductor body disposed between the source and the drain, wherein a source/body junction is defined by silicide material of the source and semiconductor material of the body and a drain/body junction is defined by silicide material of the drain and semiconductor material of the body;  
a gate electrode disposed over the body and defining a channel interposed between the source and the drain; and  
a gate dielectric separating the gate electrode and the body, said gate dielectric being made from a material having a relative permittivity greater than about 10.

21. (previously presented) A semiconductor device comprising:  
a source and a drain, said source and drain consisting of silicide;  
a semiconductor body disposed between the source and the drain;  
a gate electrode disposed over the body and defining a channel interposed between the source and the drain; and

a high-K gate dielectric separating the gate electrode and the body, said high-K gate dielectric being made from a material having a relative permittivity of greater than about 10.